

DSC2002

Silicon NPN epitaxial planar type

For general amplification
Complementary to DSA2002

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- High forward current transfer ratio h_{FE} with excellent linearity
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: C2

■ Packaging

DSC2002×0L Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	60	V
Collector-emitter voltage (Base open)	V_{CEO}	50	V
Emitter-base voltage (Collector open)	V_{EBO}	5	V
Collector current	I_C	500	mA
Peak collector current	I_{CP}	1	A
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Operating ambient temperature	T_{opr}	-40 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10 \mu\text{A}$, $I_E = 0$	60			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 2 \text{ mA}$, $I_B = 0$	50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu\text{A}$, $I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20 \text{ V}$, $I_E = 0$			0.1	μA
Forward current transfer ratio *1	h_{FE1} *2	$V_{CE} = 10 \text{ V}$, $I_C = 150 \text{ mA}$	120		340	—
	h_{FE2}	$V_{CE} = 10 \text{ V}$, $I_C = 500 \text{ mA}$	40			
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = 300 \text{ mA}$, $I_B = 30 \text{ mA}$		0.1	0.6	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}$, $I_C = 50 \text{ mA}$		160		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		4.8	15	pF

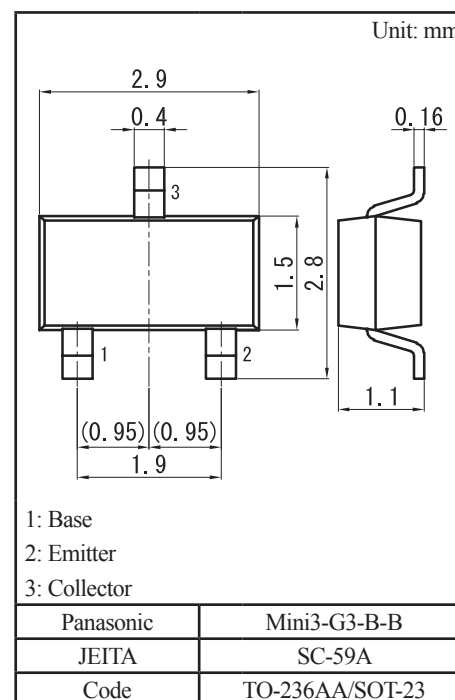
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

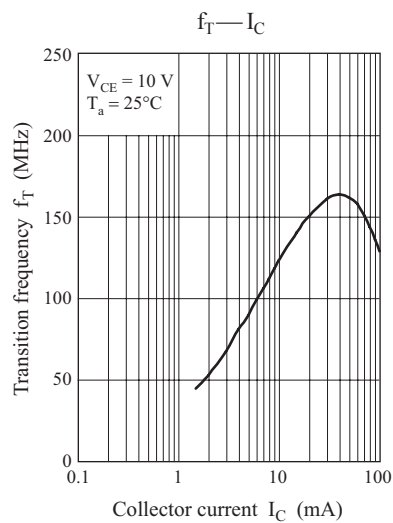
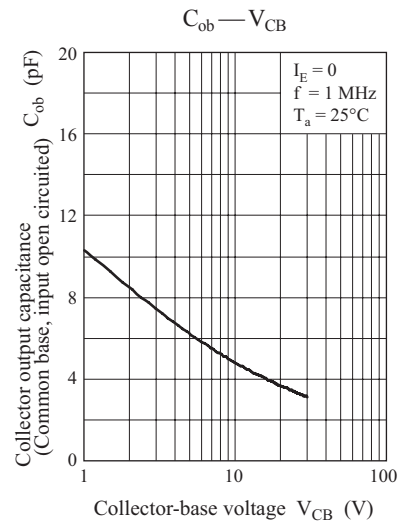
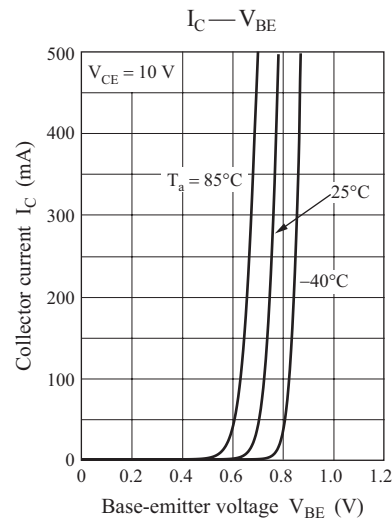
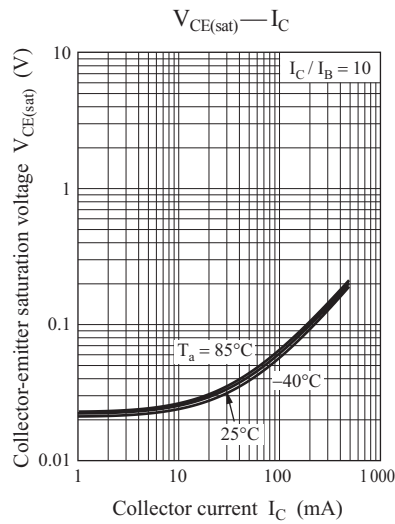
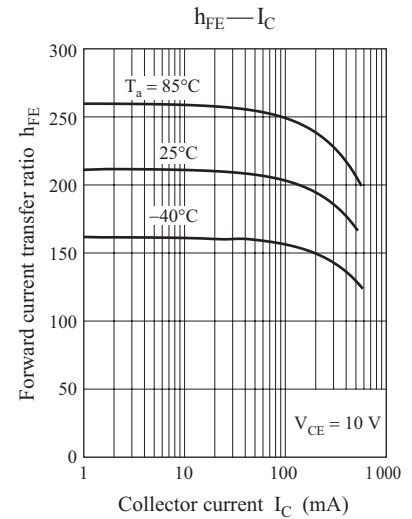
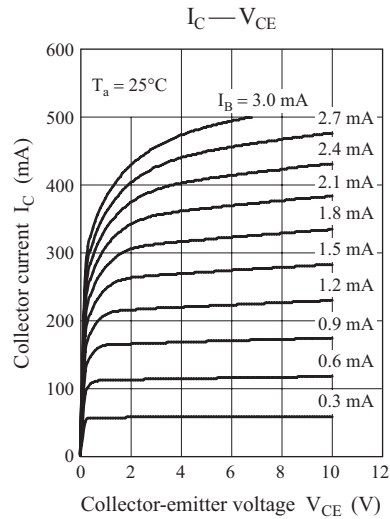
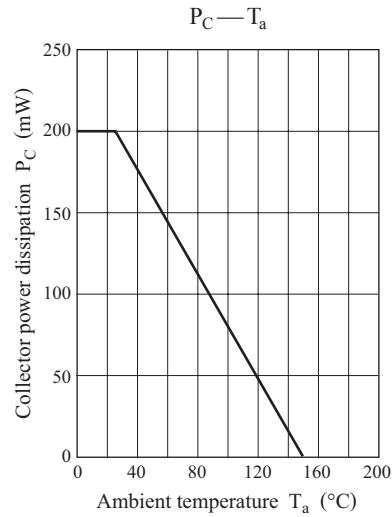
2. *1: Pulse measurement

*2: Rank classification

Code	R	S	0
Rank	R	S	No-rank
h_{FE}	120 to 240	170 to 340	120 to 340
Marking Symbol	C2R	C2S	C2

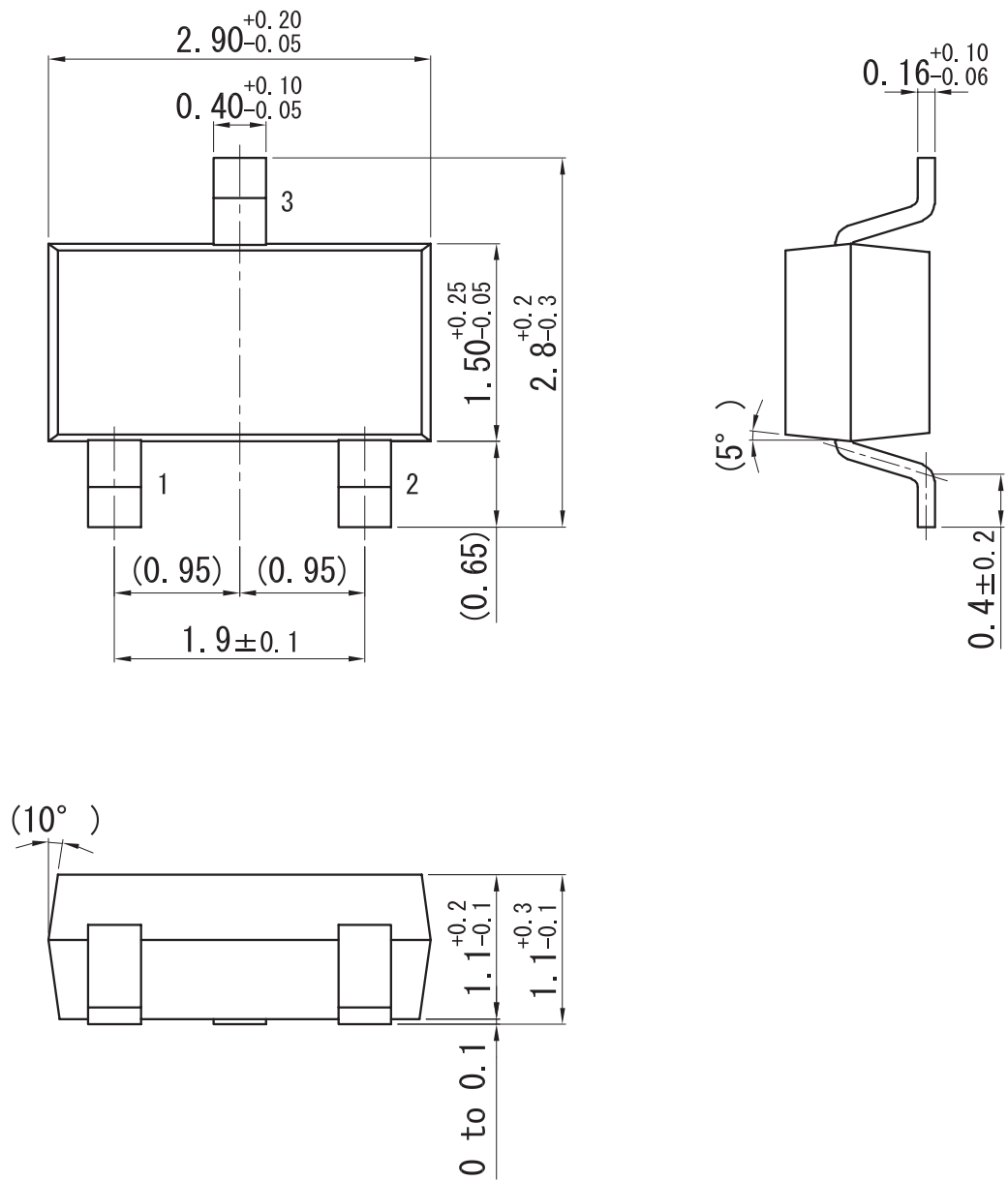
Product of no-rank is not classified and have no marking symbol for rank.



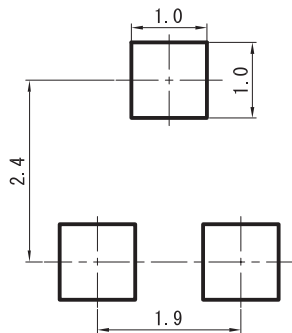


Mini3-G3-B-B

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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